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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No. : 10/509,370 Confirmation No. : 3987
First Named Inventor : Takuya SUGAWARA
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TC/A.U. : 1765
Examiner : D. V. N. Deo

Docket No. : 101249.55459US
Customer No. : 23911

Title : Method for Forming Insulation Film



SUPPLEMENTAL REPLY

Mail Stop AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

The following supplemental remarks are submitted in furtherance to the Request for Reconsideration filed on October 31, 2007.

The present invention relates to a process for forming an insulating film on the surface of a substrate. As recited in independent claim 16, the process comprises cleaning the substrate with plasma using a cleaning gas, oxidizing the substrate with plasma using an oxidizing gas to form an oxide film thereon, nitriding the oxide film with plasma using a nitriding gas and after the nitriding, treating the oxide film with plasma based on a treating gas comprising hydrogen gas.

The process according to independent claim 25 comprises cleaning the substrate with plasma using a cleaning gas, nitriding the substrate with plasma based on a nitriding gas to form a nitride film thereon, oxidizing the nitride film